

YJ Planar Schottky Barrier Diode Die Specification

60V 3A, 50mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB050M060SS-280B

Main Products Characterstics

- Average forward current: IF(AV) = 3 A
- Maximum operating junction temperature: Tj = 150 °C
- ESD rating: >8KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

IF = 3 A
Pulse Test: tp = 300 μs, δ ≤ 2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environment:

YangjieElectronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Store in original container, in dessicated nitrogen, with no contamination.

Data sheet information is subjected to change without notice.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.